ABSTRACT

The present disclosure is capable of suppressing occurrence of particles due to film separation within a process container. The present disclosure includes: (a) loading a substrate into a process container; (b) forming a film, which contains titanium and nitrogen, on the substrate by supplying a processing gas into the process container; (c) unloading the substrate after the processing out of the process container; and (d) supplying a modifying gas, which contains at least one selected from the group of silicon, metal, and halogen, into the process container after the processed substrate is unloaded from the process container.

FIG. 4A